Extended Abstracts of
the Third
International Workshop
on
Junction Technology

December 2-3, 2002
Tokyo, Japan

Sponsored by Japan Society of Applied Physics, Silicon Technology Division

Technically Cosponsored by IEEE EDS, International SEMATECH, SEMI Japan
ECS Electronics Division, and JSAP Thin Film and Surface Physics Division

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PREFACE

We are pleased to open the third IWJT (International Workshop on Junction Technology) here again in Tokyo. Thanks to the great support of the engineers and scientists in this field, the workshop has been recognized in the world as a key technical meeting regarding the junction technology and has been referenced in numbers of papers. The initial purpose of the workshop to offer an opportunity to the engineers and scientists participating in junction technologies from different specific areas - process, device, modeling, analysis, and equipment - to meet together, to exchange their knowledge and find a way for collaboration is being attained. In order to make the workshop more international, we are planning to have the next workshop in Shanghai, China in March 2004. We appreciate your continuous support and participation to the workshop.

The workshop this year consists of 8 sessions regarding device, process, modeling, measurement, and analysis technologies. Many interesting new doping techniques are presented. In this workshop, we have organized silicide sessions for the first time. Silicide is one of the key components of ultra-shallow source and drain junctions. Introduction of the silicide technologies to this workshop will make this workshop more useful.

Finally, we would like to express our sincere appreciation to the sponsors and organizations listed in the cover page, which very much supported this workshop.

December 2, 2002

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and all the committee members
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In Cooperation with
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JEITA: Japan Electronics and Information Technology Industries Association
STARC: Semiconductor Technology Academic Research Center
Selete: Semiconductor Leading Edge Technologies, Inc.
IEEJ Device Technology Group
NEDO: New Energy and Industrial Technology Development Organization
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The 3rd International Workshop on Junction Technology 2002

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